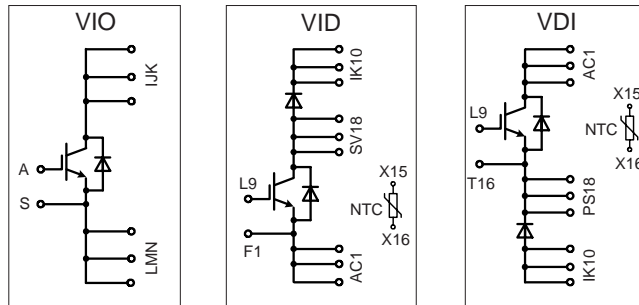


IGBT Modules in ECO-PAC 2

Short Circuit SOA Capability
 Square RBSOA

$I_{C25} = 138 \text{ A}$
 $V_{CES} = 1200 \text{ V}$
 $V_{CE(sat) \text{ typ.}} = 2.8 \text{ V}$

Preliminary data sheet



Pin arrangement see outlines

IGBTs			
Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^\circ\text{C to } 150^\circ\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^\circ\text{C}$	138	A
I_{C80}	$T_C = 80^\circ\text{C}$	94	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15 \text{ V}; R_G = 15 \Omega; T_{VJ} = 125^\circ\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	150	A
		V_{CES}	
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 15 \Omega; T_{VJ} = 125^\circ\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^\circ\text{C}$	568	W

Features

- NPT IGBT's
 - positive temperature coefficient of saturation voltage
 - fast switching
- FRED diodes
 - fast reverse recovery
 - low forward voltage
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated DCB ceramic base plate

Advantages

- space and weight savings
- reduced protection circuits
- leads with expansion bend for stress relief

Typical Applications

- AC and DC motor control
- AC servo and robot drives
- power supplies
- welding inverters

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^\circ\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 125 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.8	3.4	V	
			3.2	V	
$V_{GE(th)}$	$I_C = 3 \text{ mA}; V_{GE} = V_{CE}$	4.5		V	
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$		5	mA	
				16	mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			320 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^\circ\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 75 \text{ A}$ $V_{GE} = 15/0 \text{ V}; R_G = 15 \Omega$		100	ns	
				50	ns
				650	ns
				50	ns
				12.1	mJ
				10.5	mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		5.5	nF	
R_{thJC} R_{thJH}	(per IGBT) with heatsink compound ($0.42 \text{ K/m.K}; 50 \mu\text{m}$)		0.44	0.22 K/W K/W	

IXYS reserves the right to change limits, test conditions and dimensions.

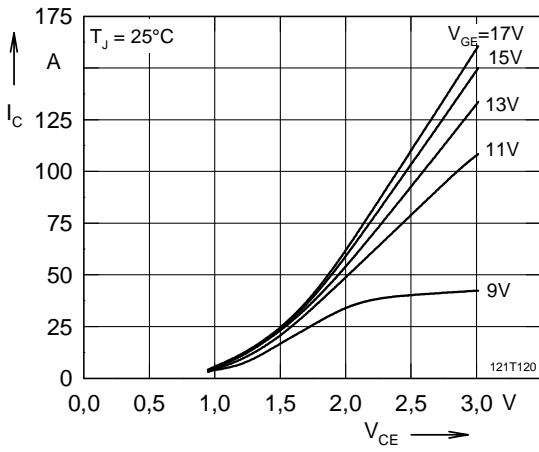


Fig. 1 Typ. output characteristics

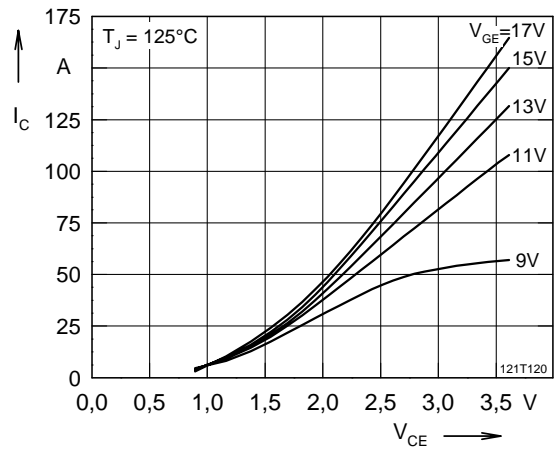


Fig. 2 Typ. output characteristics

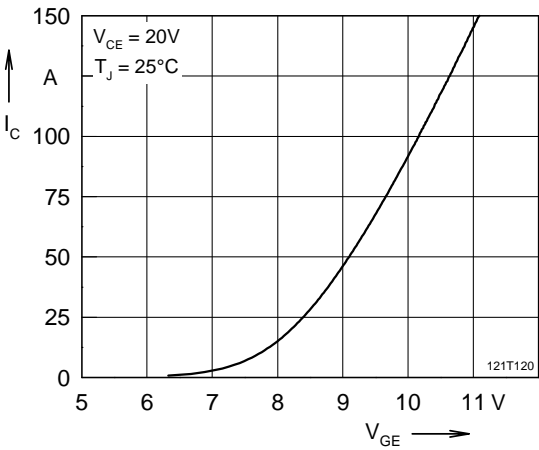


Fig. 3 Typ. transfer characteristics

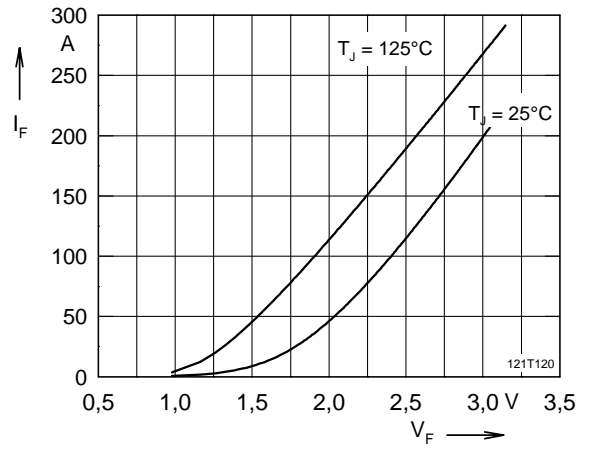


Fig. 4 Typ. forward characteristics of free wheeling diode

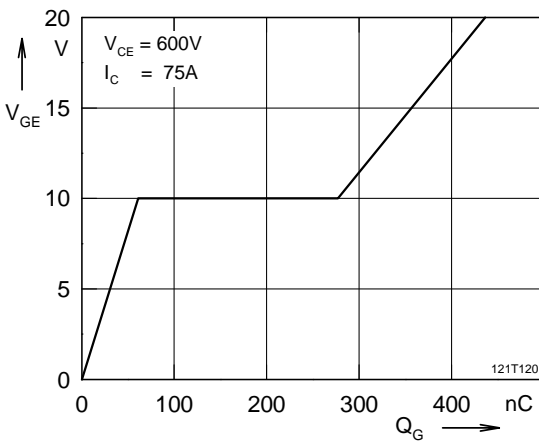


Fig. 5 Typ. turn on gate charge

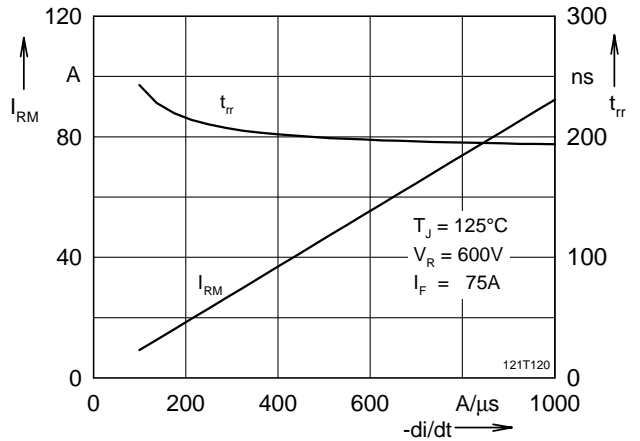


Fig. 6 Typ. turn off characteristics of free wheeling diode

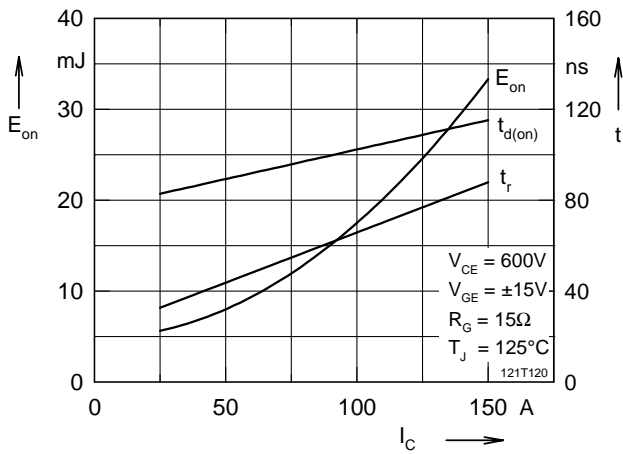


Fig. 7 Typ. turn on energy and switching times versus collector current

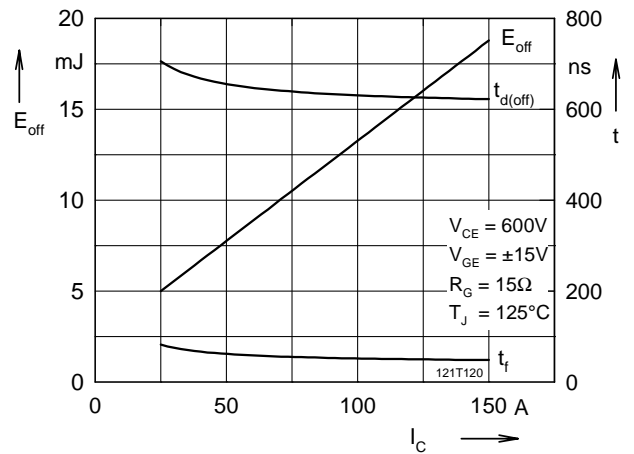


Fig. 8 Typ. turn off energy and switching times versus collector current

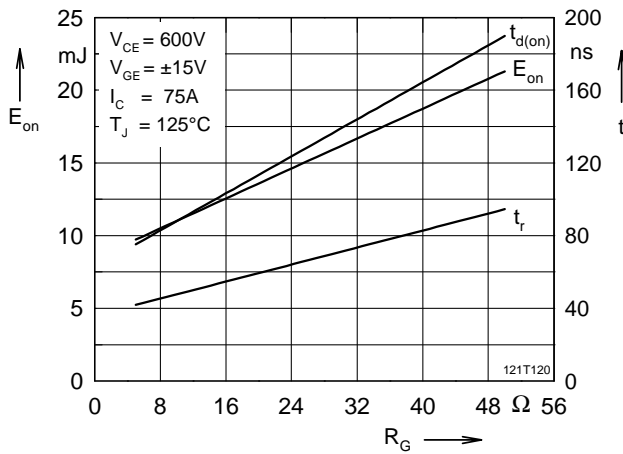


Fig. 9 Typ. turn on energy and switching times versus gate resistor

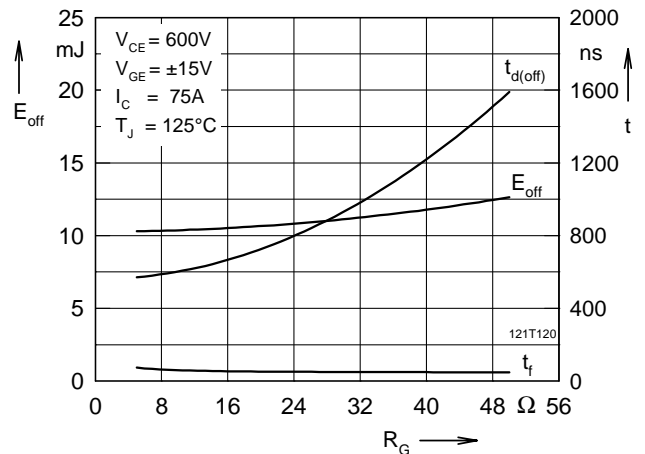


Fig. 10 Typ. turn off energy and switching times versus gate resistor

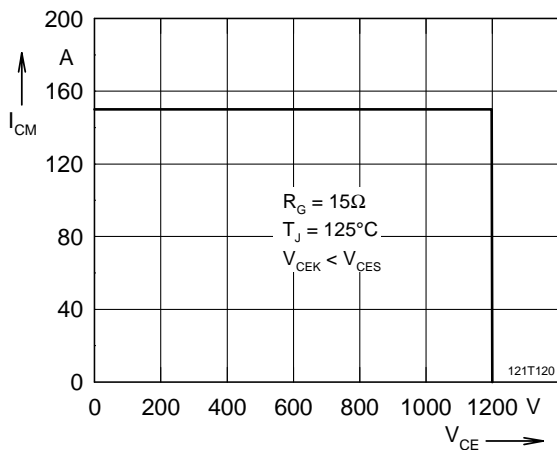


Fig. 11 Reverse biased safe operating area RBSOA

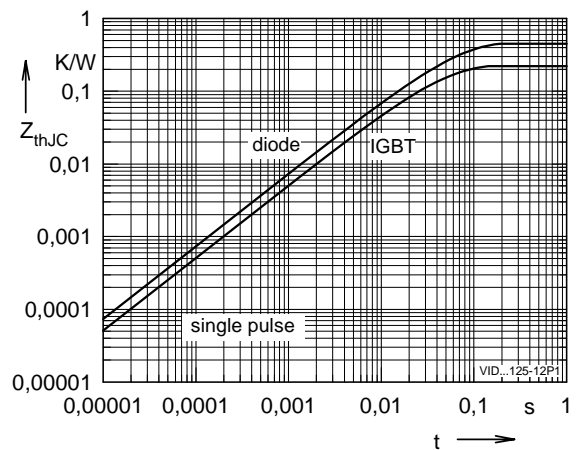


Fig. 12 Typ. transient thermal impedance